PNP SILICON PLANAR MEDIUM POWER TRANSISTORS IN SOT89

Features

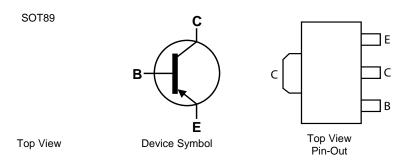
- I_C = -1A Continuous Collector Current
- Low Saturation Voltage V_{CE(sat)} < -500mV @ -0.5A
- Gain groups 10 and 16
- Epitaxial Planar Die Construction
- Complementary NPN types: BCX54, 55, and 56
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Devices (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound (Note 2)
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.072 grams (Approximate)

Applications

- Medium Power Switching or Amplification Applications
- AF driver and output stages



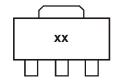
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCX51TA	AA	7	12	1,000
BCX5110TA	AC	7	12	1,000
BCX5116TA	AD	7	12	1,000
BCX52TA	AE	7	12	1,000
BCX5210TA	AG	7	12	1,000
BCX5216TA	AM	7	12	1,000
BCX53TA	AH	7	12	1,000
BCX5310TA	AK	7	12	1,000
BCX5316TA	AL	7	12	1,000
BCX5316TC	AL	13	12	4,000
BCX5316-13R	AL	13	12	4,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website http://www.diodes.com

Marking Information



xx = Product Type Marking Code, as follows:

BCX51 = AA	BCX52 = AE	BCX53 = AH
BCX5110 = AC	BCX5210 = AG	BCX5310 = AK
BCX5116 = AD	BCX5316 = AM	BCX5316 = AL

Maximum Ratings @ T_A = 25℃ unless otherwise specified

Characteristic	Symbol	BCX51	BCX52	BCX53	Unit
Collector-Base Voltage	V _{CBO}	-45	-60	-100	V
Collector-Emitter Voltage	V _{CEO}	-45	-60	-80	V
Emitter-Base Voltage	V _{EBO}		V		
Continuous Collector Current	Ic	-1			^
Peak Pulse Collector Current	I _{CM}		A		
Continuous Base Current	I _B	-100			A
Peak Pulse Base Current	I _{BM}	-200			mA mA

Thermal Characteristics @ TA = 25°C unless otherwise specified

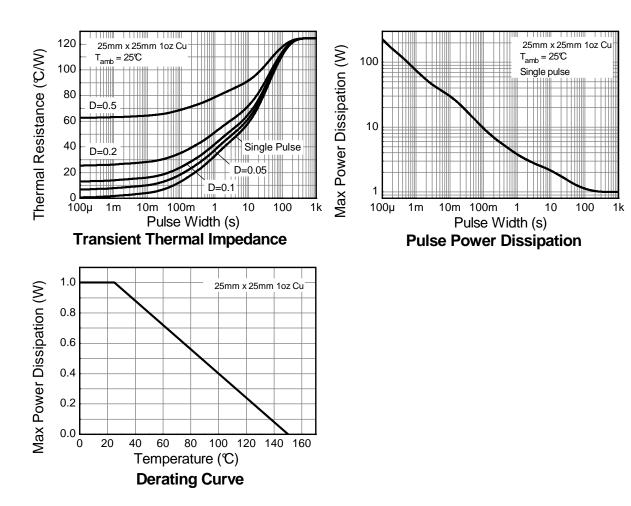
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 4)	R _{0JA}	124	°C/W
Thermal Resistance, Junction to Leads (Note 5)	R _{θJL}	10.0	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Notes:

^{4.} For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

5. Thermal resistance from junction to solder-point (on the exposed collector pad).

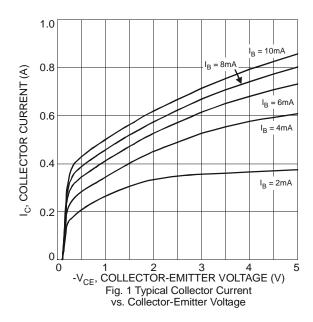
Thermal Characteristics

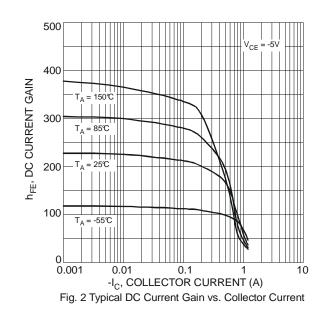


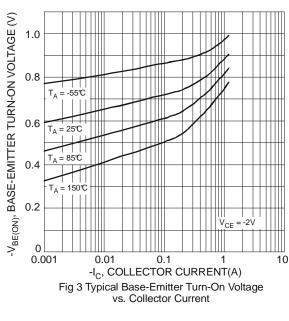
Electrical Characteristics @ T_A = 25°C unless otherwise specified

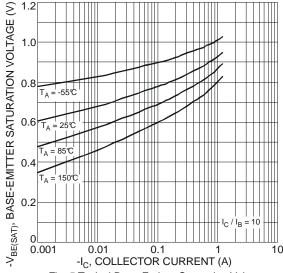
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Callector Dage	BCX51		-45				
Collector-Base Breakdown Voltage	BCX52	BV _{CBO}	-60	-	-	V	I _C = -100μA
breakdown voltage	BCX53		-100				
Collector-Emitter	BCX51		-45				
Breakdown Voltage (Note 6)	BCX52	BV _{CEO}	-60	-	-	V	$I_C = -10mA$
Breakdown Voltage (Note o)	BCX53		-80				
Emitter-Base Breakdown Voltage		BV _{EBO}	-5	-	-	V	$I_E = -10\mu A$
Collector Cut-off Current		I _{CBO}	-	ı	-0.1 -20	μΑ	V _{CB} = -30V
Collector Cut-on Current							V _{CB} = -30V, T _A = 150℃
Emitter Cut-off Current		I _{EBO}	-	-	-20	nA	$V_{EB} = -4V$
	All versions	h _{FE}	25	-	-		$I_C = -5mA$, $V_{CE} = -2V$
			40	-	250		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 6)			25	-	-		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
, in the second of the second	10 gain grp]	63	-	160		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
	16 gain grp	1	100	-	250		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
Collector-Emitter Saturation Voltage (Note 6)		V _{CE(sat)}	-	-	-0.5	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-On Voltage (Note 6)		V _{BE(on)}	-	-	-1.0	V	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
Transition Frequency		f⊤	150	-	-	MHz	I _C = -50mA, V _{CE} = -10V f = 100MHz
Output Capacitance		Cobo	-	-	25	pF	$V_{CB} = -10V$, $f = 1MHz$

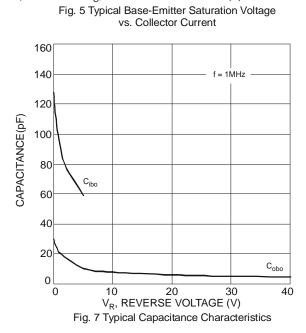
Notes: 6. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.











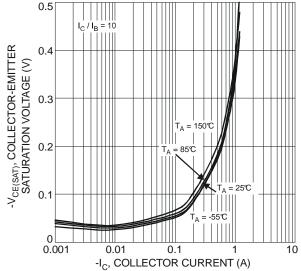


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

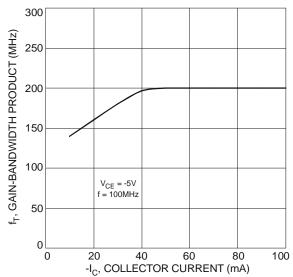
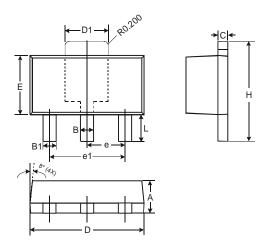


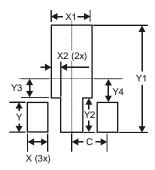
Fig. 6 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.43		
D	4.40	4.60		
D1	1.52	1.83		
Е	2.29 2.60			
е	1.50 Typ			
e1	3.00 Typ			
Н	3.94 4.25			
L	0.89	1.20		
All [All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)		
Х	0.900		
X1	1.733		
X2	0.416		
Y	1.300		
Y1	4.600		
Y2	1.475		
Y3	0.950		
Y4	1.125		
C	1.500		

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